TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC5076

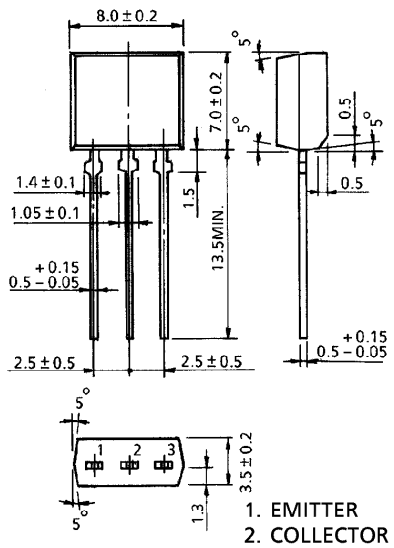
HIGH CURRENT SWITCHING APPLICATIONS

- Low Collector Saturation Voltage : $V_{CE\ (sat)}$ = 0.4V (Max.) (at I_C = 3A)
- High Speed Switching Time : t_{stg} = 1.0 μs (Typ.)
- Complementary to 2SA1905

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	5	A
Base Current	I_B	1	A
Collector Power Dissipation	P_C	1.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

Unit in mm

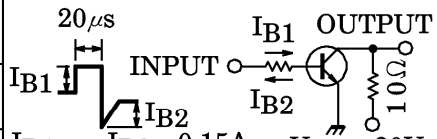


JEDEC	—
EIAJ	—
TOSHIBA	2-8M1A

Weight : 0.55g

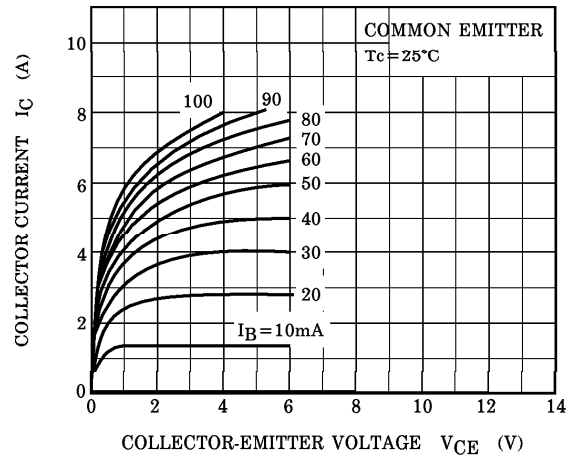
961001EAA2

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

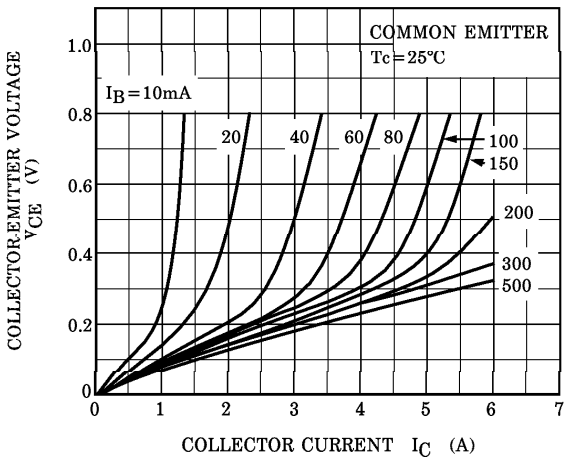
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 50V, I_E = 0	—	—	1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 5V, I_C = 0	—	—	1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	50	—	—	V
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE} = 1V, I_C = 1A	70	—	240	
		$h_{FE(2)}$	V_{CE} = 1V, I_C = 3A	30	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C = 3A, I_B = 0.15A	—	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$	I_C = 3A, I_B = 0.15A	—	0.9	1.2	
Transition Frequency		f_T	V_{CE} = 4V, I_C = 1A	—	120	—	MHz
Collector Output Capacitance		C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	80	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.1	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	0.1	—	

Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

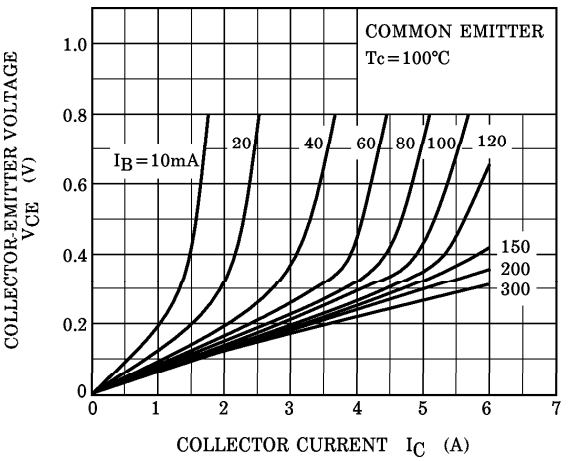
IC – VCE



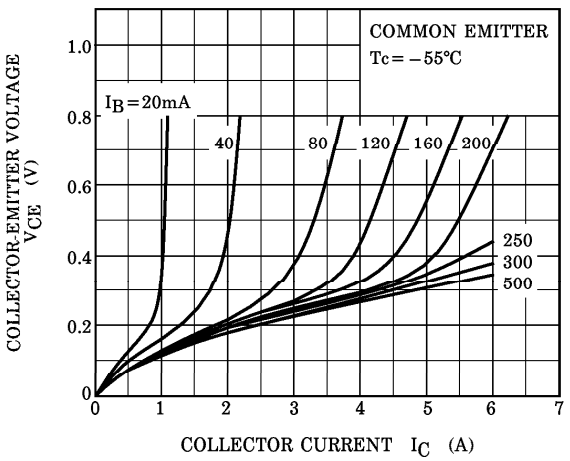
VCE – IC



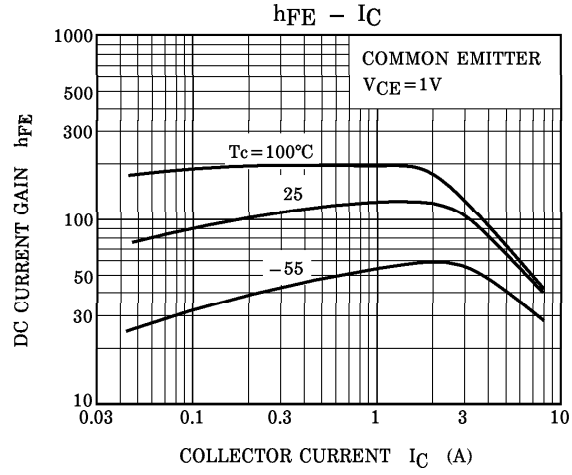
VCE – IC



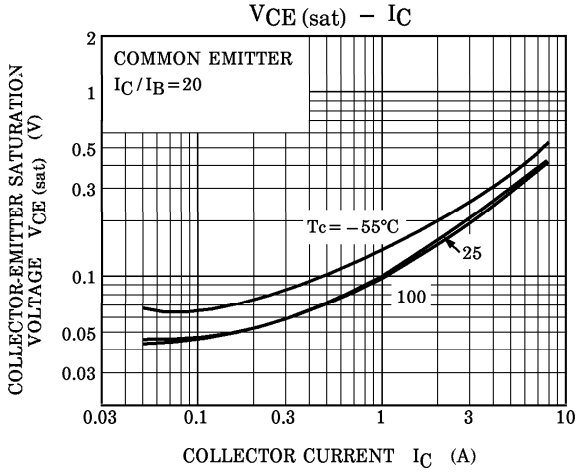
VCE – IC



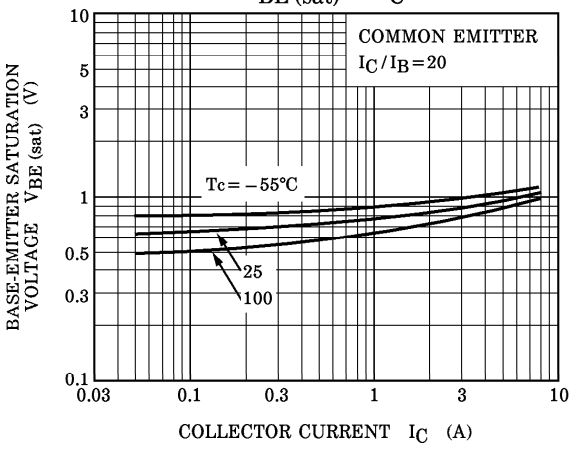
hFE – IC



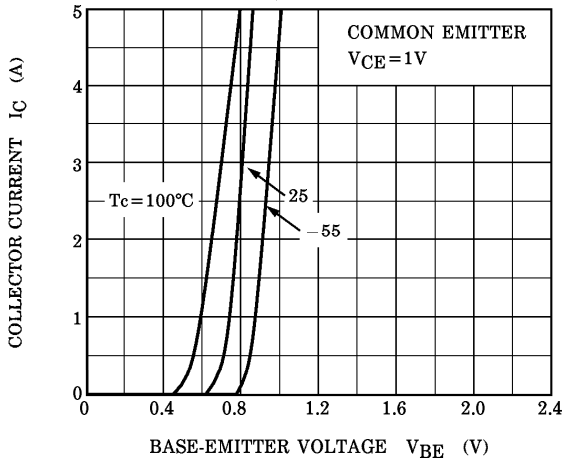
VCE (sat) – IC



$V_{BE\,(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA